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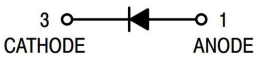
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Switching Diode

Features

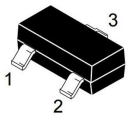
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant



MAXIMUM RATINGS

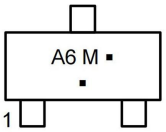
Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	100	V
Peak Forward Current	I_F	200	mA
Non−Repetitive Peak Forward Surge Current 60 Hz	$I_{FSM(surge)}$	500	mA
Repetitive Peak Forward Current (Note 3)	I_{FRM}	1.0	A
Non−Repetitive Peak Forward Current (Square Wave, T_J = 25°C prior to surge) t = 1 μs t = 10 μs t = 100 μs t = 1 ms t = 1 s	I_{FSM}	 36.0 18.0 6.0 3.0 0.7	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



SOT−23

MARKING DIAGRAM



A6 = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	 225 1.8	 mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	 300 2.4	 mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.
3. Square Wave, f = 40 kHz, PW = 200 ns
   Test Duration = 60 s, T_J = 25°C prior to surge.

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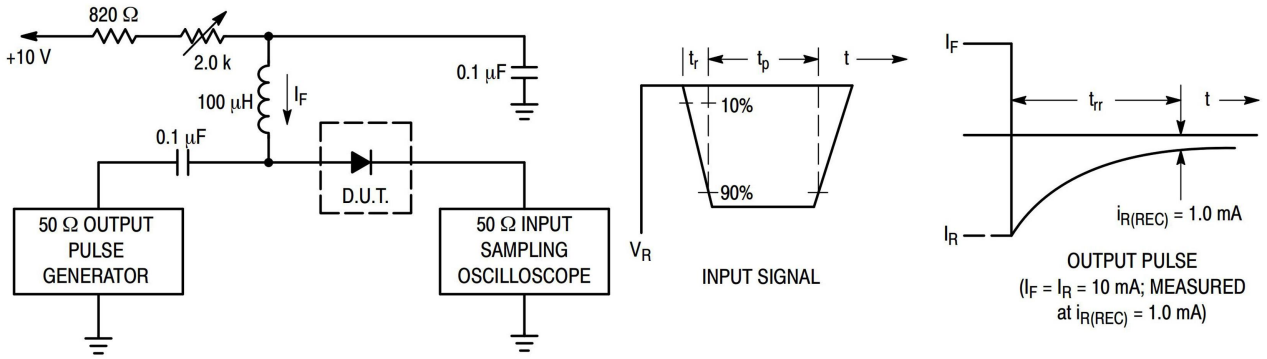
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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current	I_R			μAdc
(V_R = 100 V)		–	1.0	
(V_R = 75 Vdc, T_J = 150°C)		–	50	
(V_R = 25 Vdc, T_J = 150°C)		–	30	
Reverse Breakdown Voltage (I_{BR} = 100 μAdc)	$V_{(BR)}$	100	–	Vdc
Forward Voltage	V_F			mV
(I_F = 1.0 mAdc)		–	715	
(I_F = 10 mAdc)		–	855	
(I_F = 50 mAdc)		–	1000	
(I_F = 150 mAdc)		–	1250	
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	–	2.0	pF
Forward Recovery Voltage (I_F = 10 mAdc, t_r = 20 ns)	V_{FR}	–	1.75	Vdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, R_L = 50 Ω)	t_{rr}	–	6.0	ns
Stored Charge (I_F = 10 mAdc to V_R = 5.0 Vdc, R_L = 500 Ω)	Q_S	–	45	pC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

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TYPICAL CHARACTERISTICS

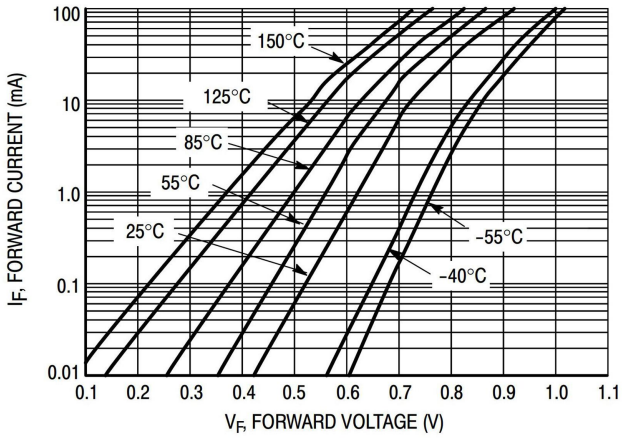


Figure 2. V_F vs. I_F

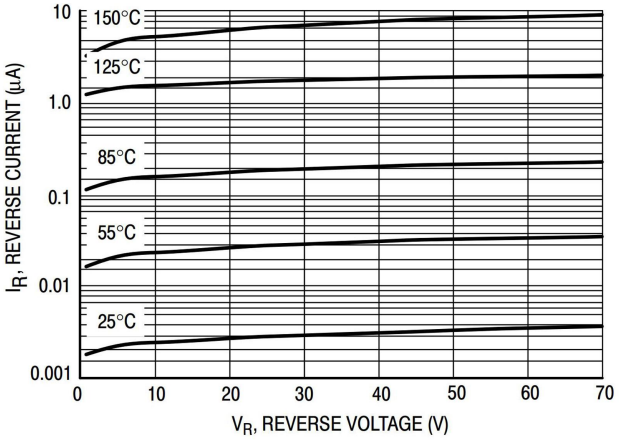


Figure 3. I_R vs. V_R

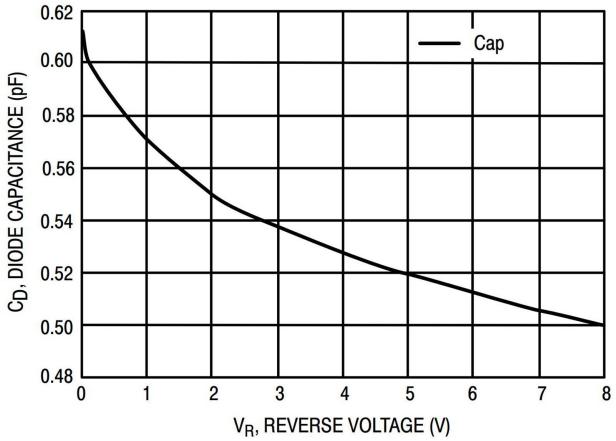


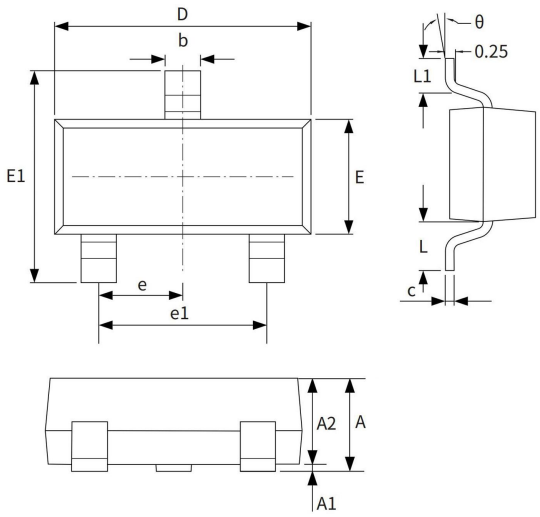
Figure 4. Capacitance

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Ordering Information

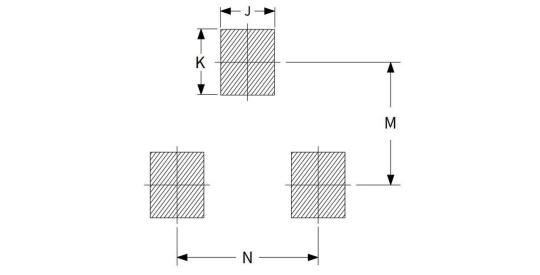
PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23	R1	0.008	3000	30000	240000	7''

Package Outline Dimensions (SOT-23)



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.15	0.035	0.045
A1	-	0.10	-	0.004
A2	0.90	1.05	0.035	0.041
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.80	2.00	0.071	0.079
L	0.550REF		0.022REF	
L1	0.30	0.50	0.012	0.020
θ	-	8°	-	8°

Suggested Pad Layout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	0.75	0.85	0.030	0.033
K	0.85	0.95	0.033	0.037
M	1.95	2.05	0.077	0.081
N	1.85	1.95	0.073	0.077